

#### **Description**

The H2N7002K7 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

# D G S

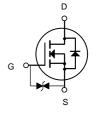
SOT-23

#### **General Features**

 $V_{DS} = 60V I_{D} = 0.3A$ 

 $R_{DS(ON)} < 2\Omega$  @  $V_{GS}=10V$ 

ESD Rating: HBM≥2000V



N-Channel MOSFET

#### **Application**

Battery protection

Load switch

Uninterruptible power supply

# **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
H2N7002K7	SOT-23	72K/7002	3000

# Absolute Maximum Ratings (T<sub>C</sub>=25°Cunless otherwise noted)

Symbol	Parameter	Limit	Unit	
V <sub>DS</sub>	Drain-Source Voltage		60	V
V <sub>G</sub> S	Gate-Source Voltage	e-Source Voltage		V
		T <sub>A</sub> =25℃	0.3	
$I_D$	Continuous Drain Current (T <sub>J</sub> =150℃)	T <sub>A</sub> =100℃	0.19	А
Ірм	Drain Current-Pulsed (Note 1)		0.8	Α
P <sub>D</sub>	Maximum Power Dissipation		0.35	W
TJ,Tstg	Operating Junction and Storage Temperature Range		-55 To 150	$^{\circ}$ C
RеJA	Thermal Resistance,Junction-to-Ambient (Note 2)		350	°C/W



#### Electrical Characteristics (T<sub>A</sub>=25 ℃unless otherwise noted)

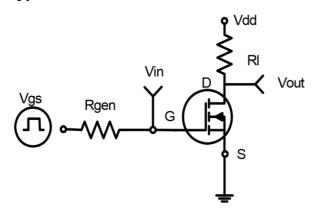
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	60	68	-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	Igss	V <sub>GS</sub> =±10V,V <sub>DS</sub> =0V	-	±100	±500	nA
		V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	±4	±10	uA
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	0.7	1.2	1.9	V
		V <sub>GS</sub> =5V, I <sub>D</sub> =0.1A	-	1.3	3	Ω
Drain-Source On-State Resistance	RDS(ON)	V <sub>GS</sub> =10V, I <sub>D</sub> =0.1A	-	1	2	Ω
Forward Transconductance	grs	V <sub>DS</sub> =10V,I <sub>D</sub> =0.2A	0.1	-	-	S
Input Capacitance	C <sub>lss</sub>		-	21	50	PF
Output Capacitance	Coss	$V_{DS}$ =25V, $V_{GS}$ =0V, F=1.0MHz	-	11	25	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	1 – 1.0IVII 12	-	4.2	5	PF
Turn-on Delay Time	td(on)		-	10	-	nS
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> =30V,I <sub>D</sub> =0.2A	-	50	-	nS
Turn-Off Delay Time	td(off)	V <sub>GS</sub> =10V,R <sub>GEN</sub> =10Ω	-	17	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
		V <sub>DS</sub> =10V,I <sub>D</sub> =0.3A,				
Total Gate Charge	Qg	V <sub>GS</sub> =4.5V	-	1.7	3	nC
Diode Forward Voltage (Note 3)	Vsp	V <sub>GS</sub> =0V,I <sub>S</sub> =0.2A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	0.3	Α

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



### **Typical Electrical And Thermal Characteristics**



**Figure 1:Switching Test Circuit** 

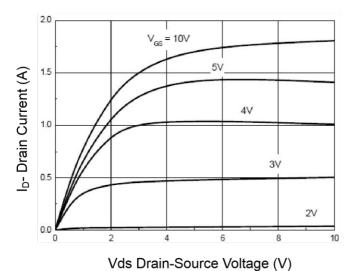


Figure 3 Output Characteristics

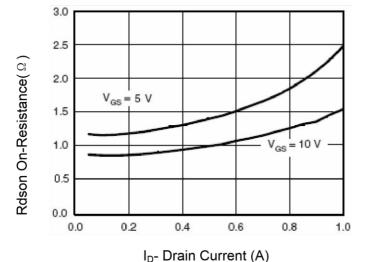


Figure 5 Drain-Source On-Resistance

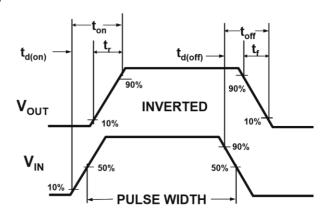


Figure 2:Switching Waveforms

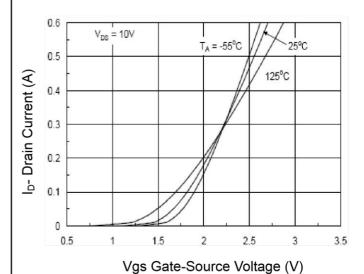
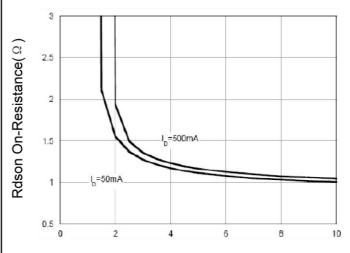
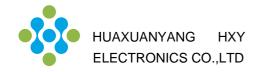
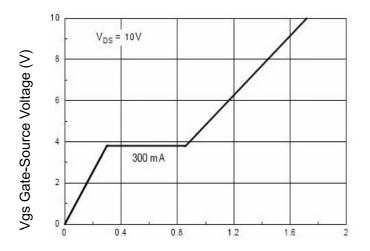


Figure 4 Transfer Characteristics

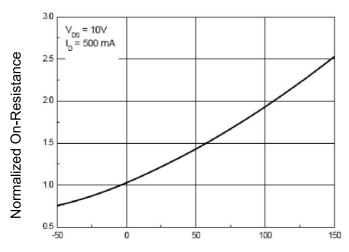


Vgs Gate-Source Voltage (V)
Figure 6 Rdson vs Vgs





Qg Gate Charge (nC) Figure 7 Gate Charge



 $T_J$ -Junction Temperature( ${}^{\circ}C$ )
Figure 9 Drain-Source On-Resistance

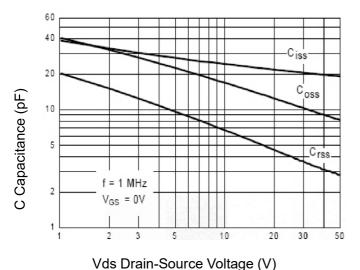


Figure 11 Capacitance vs Vds

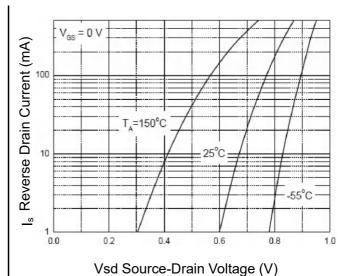
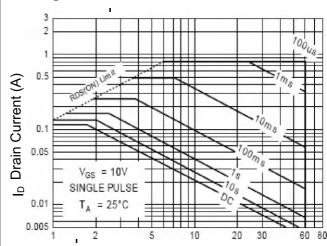
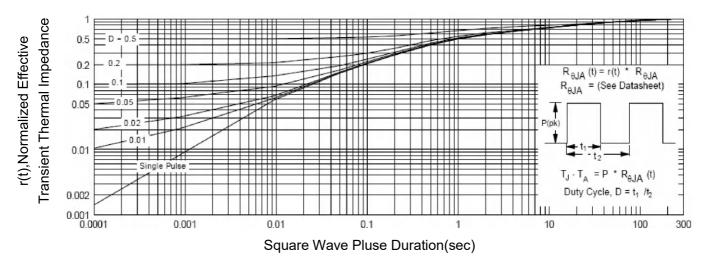


Figure 8 Source-DrainDiode Forward



Vds Drain-Source Voltage (V)

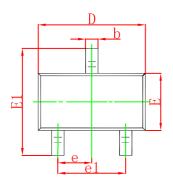
Figure 10 Safe Operation Area

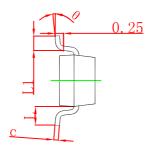


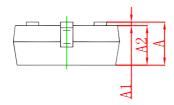
**Figure 12 Normalized Maximum Transient Thermal Impedance** 



# **SOT-23 Package Outline Dimensions**

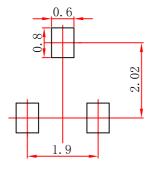






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	0 TYP 0.037 TYP		7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



- Note:
  1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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